

Supporting Information

Flexible Polymer Solar Cells with Power Conversion Efficiency of 8.7%

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The sheet resistance of the PET/ITO as a function of bending angle and bending cycle test for a typical PTB7 devices (after storing in N₂ atmosphere for 150 days)

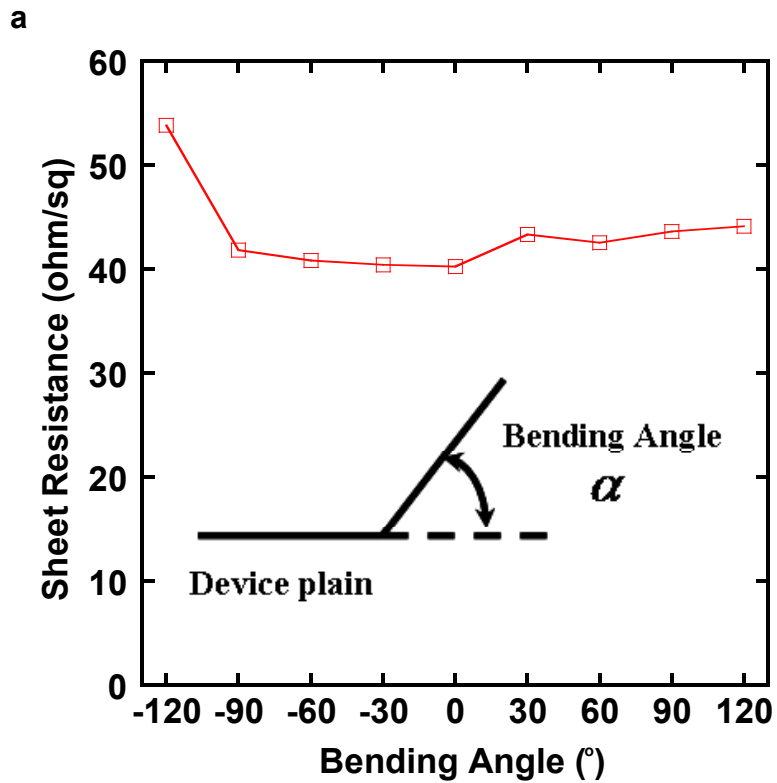
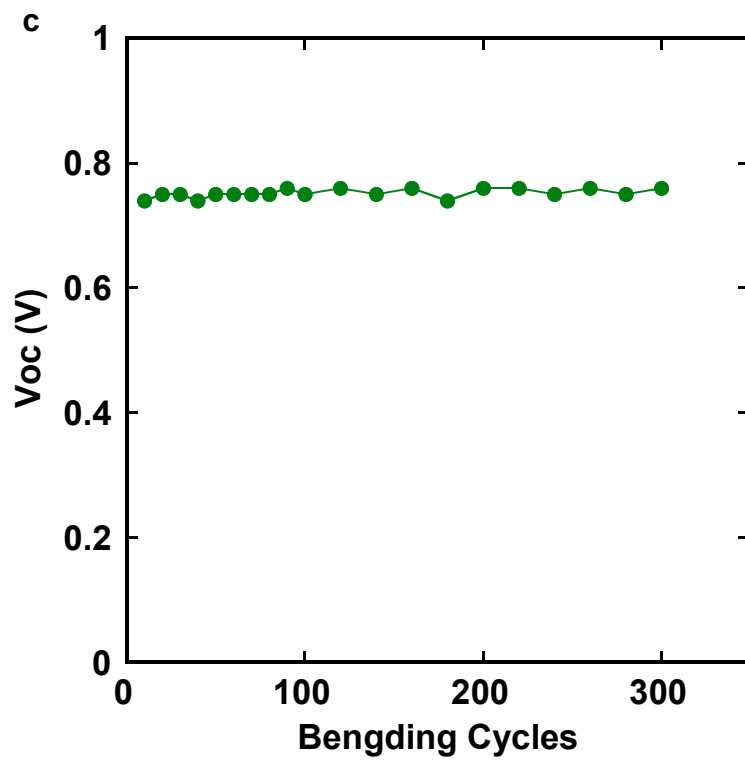
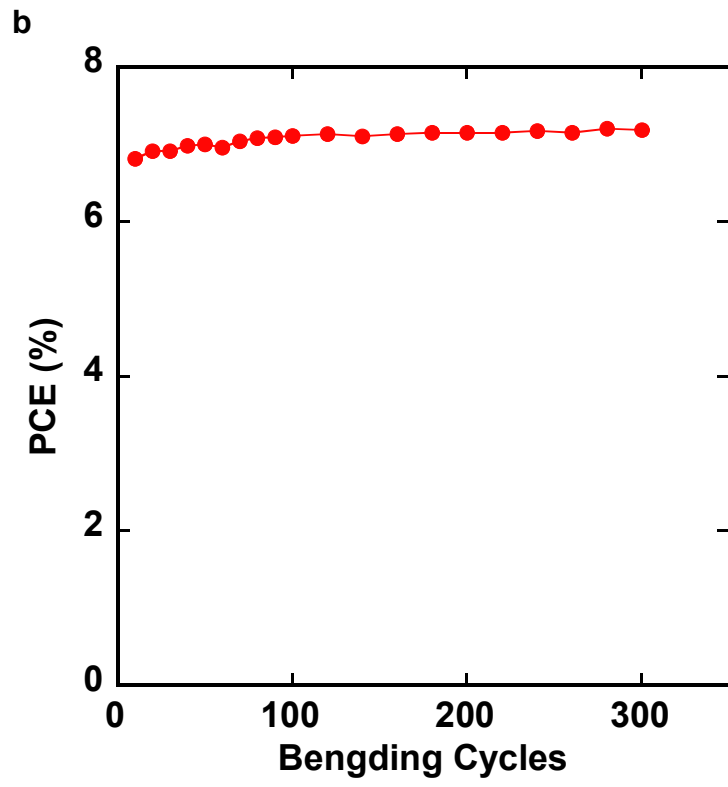


Figure S1. a) the sheet resistance of the PET/ITO under different bending conditions. Note that the unfolded substrate showed a sheet resistance of 40 ohm/square.



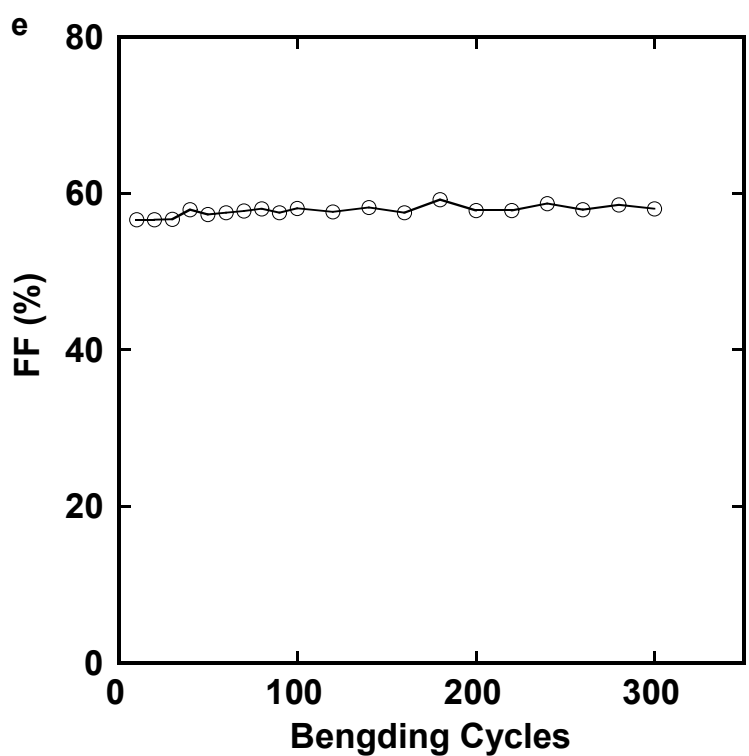
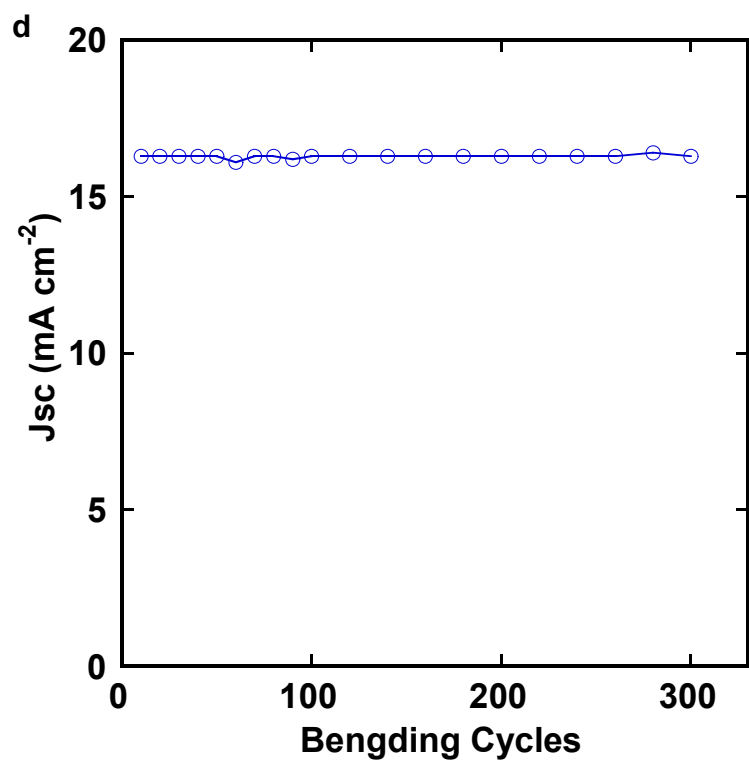


Figure S1. b)~e). The PCE (b), Voc (c), Jsc (d) and FF (e) of the a typical PTB7 devices (stored in N₂ atmosphere for 150 days) for as a function of bending cycles at fixed bending angle of 30 °.

***J-V* characteristics and performance parameters of a typical flexible Device 2 during shelf storage**

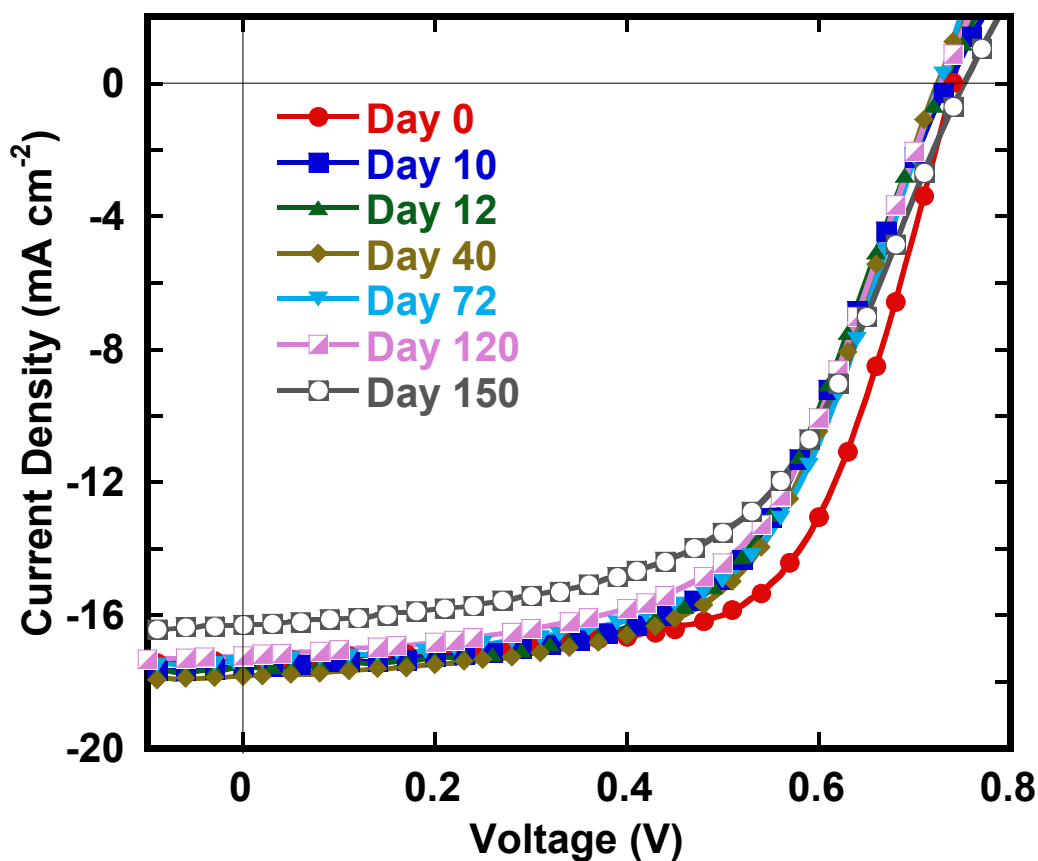


Figure S2. The *J-V* characteristics of a typical flexible Device 2 obtained during shelf storage period.

Table S2. Device performance parameters of a typical Device 2 tested during different shelf storage period.

| Days | Voc [V] | Jsc [mA cm ⁻²] | FF [%] | PCE [%] |
|------|------------|-------------------------------|-----------|------------|
| 0 | 0.74 | 17.4 | 64.4 | 8.28 |
| 10 | 0.74 | 17.5 | 57.6 | 7.47 |
| 12 | 0.73 | 17.6 | 57.9 | 7.45 |
| 40 | 0.72 | 17.8 | 59.5 | 7.64 |
| 72 | 0.73 | 17.4 | 59.3 | 7.53 |
| 120 | 0.72 | 17.2 | 58.4 | 7.24 |
| 150 | 0.75 | 16.3 | 55.9 | 6.83 |

***J-V* characteristics and performance parameters of a typical flexible
Device 2 upon thermal annealing**

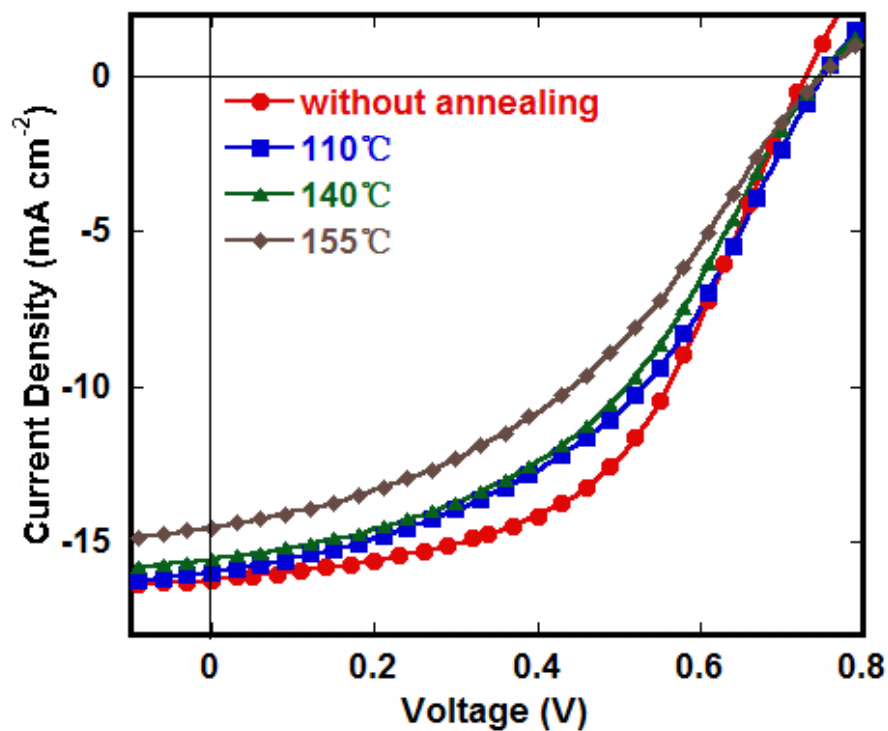


Figure S3. The *J-V* characteristics of a typical device 2 after 110, 140 and 155°C annealing for 10 min.

Table S3. Device performance parameters of a typical Device 2 (after storage for more than 150 days)

| Post-thermal annealing | Voc | Jsc | FF | PCE |
|------------------------|------|------------------------|------|------|
| | [V] | [mA cm ⁻²] | [%] | [%] |
| N.A. | 0.73 | 16.2 | 52.1 | 6.17 |
| 110°C 10 min | 0.75 | 16 | 45.2 | 5.42 |
| 140°C 10 min | 0.75 | 15.5 | 44.6 | 5.20 |
| 155°C 10 min | 0.75 | 14.9 | 43.6 | 4.88 |